## 10656727 CLS

Most Frequently Occurring Classifications of Patents Returned From A Search of 10656727 on May 03, 2004

# Original Classifications

- 4 250/504R
- 2 250/492.2
- 2 313/491
- 2 355/30
- 2 355/53
- 2 378/119
- 2 378/34

#### Cross-Reference Classifications

- 4 250/493.1
- 3 250/492.2
- 3 313/574
- 3 355/67
- 2 257/E21.035
- 2 257/E21.279
- 2 313/618
- 2 313/632
- 2 378/119

## Combined Classifications

- 5 250/492.2
- 5 250/493.1
- 5 250/504R
- 4 378/119
- 3 313/491
- 3 313/574
- 3 313/632
- 3 355/53
- 3 355/67
- 3 378/34
- 2 250/574
- 2 257/E21.035
- 2 257/E21.279
- 2 313/618
- 2 355/30
- 2 356/338

### 10656727 CLSTITLES

Titles of Most Frequently Occurring Classifications of Patents Returne

From A Search of 10656727 on May 03, 2004

```
5 250/492.2
                (2 OR, 3 XR)
       Class 250: RADIANT ENERGY
       250/492.1
                     IRRADIATION OF OBJECTS OR MATERIAL
                    .Irradiation of semiconductor devices
       250/492.2
               (1 OR, 4 XR)
5 250/493.1
       Class
               250 : RADIANT ENERGY
                     RADIANT ENERGY GENERATION AND SOURCES
       250/493.1
5 250/504R
                (4 OR, 1 XR)
       Class 250: RADIANT ENERGY
       250/493.1 RADIANT ENERGY GENERATION AND SOURCES 250/503.1 .With radiation modifying member
       250/504R
                    ..Ultraviolet or infrared source
               (2 OR, 2 XR)
4 378/119
       Class 378: X-RAY OR GAMMA RAY SYSTEMS OR DEVICES
       378/119
                     SOURCE
3 313/491
                (2 OR, 1 XR)
       Class 313: ELECTRIC LAMP AND DISCHARGE DEVICES
                     WITH LUMINESCENT SOLID OR LIQUID MATERIAL
       313/483
       313/484
                    .With gaseous discharge medium
       313/485
                     .. Phosphor on envelope wall
       313/491
                      ... Electrode structure or material
3 313/574
                (0 \text{ OR}, 3 \text{ XR})
               313 : ELECTRIC LAMP AND DISCHARGE DEVICES
       Class
                     WITH GAS OR VAPOR
       313/567
       313/568
                     .Having a particular total or partial pressure
       313/572
                     ..One torr thru 760 torr
       313/574
                     ...With electrode structure
               (1 OR, 2 XR)
3 313/632
       Class 313: ELECTRIC LAMP AND DISCHARGE DEVICES
       313/567
                     WITH GAS OR VAPOR
                    .Having particular electrode structure
       313/631
                     ..Cathode or anode
       313/632
3 355/53
               (2 OR, 1 XR)
```

PROJECTION PRINTING AND COPYING CAMERAS

Class 355: PHOTOCOPYING

355/18

#### 10656727 CLSTITLES 355/53 .Step and repeat 3 355/67 (0 OR, 3 XR)355 : PHOTOCOPYING Class 355/18 PROJECTION PRINTING AND COPYING CAMERAS 355/67 .Illumination systems or details 3 378/34 (2 OR, 1 XR) 378 : X-RAY OR GAMMA RAY SYSTEMS OR DEVICES Class 378/1 SPECIFIC APPLICATION 378/34 .Lithography 2 250/574 (1 OR, 1 XR)Class 250: RADIANT ENERGY 250/200 PHOTOCELLS; CIRCUITS AND APPARATUS 250/216 .Optical or pre-photocell system 250/573 .. Fluent material in optical path 250/574 ...Scattered or reflected light 2 257/E21.035 (0 OR, 2 XR) 257 : ACTIVE SOLID-STATE DEVICES Class 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO) 257/E21.002 .Manufacture or treatment of semiconductor device (EPO) .. Making mask on semicond uctor body for 257/E21.023 further photolithographic processing (EPO 257/E21.033 ...Comprising inorganic layer (EPO) 257/E21.035 .... Characterized by their composition, e.g., multilayer masks, materials (EPO) 257/E21.279 (0 OR, 2 XR) 257 : ACTIVE SOLID-STATE DEVICES 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO) 257/E21.002 .Manufacture or treatment of semiconductor device (EPO) 257/E21.04 .. Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion

)

layer, carrier concentration layer

### 10656727 CLSTITLES

(EDO)		10656727_CLSTITLES
(EPO)	257/E21.085 .	Device having semiconductor body comprising Group IV elements or Group III-V co
mpounds with or without		
(EPO)		impurities, e.g., doping materials
		Treatment of semiconductor body using process other than deposition of sem
iconductor material on a substrate, diffusion or alloying o		
f impurity material, or		
		radiation treatment (EPO)To change their surface-physical characteristics or shape, e.g., etchi
ng, polishing, cutting		
	257/E21.24 .	<pre>(EPO)To form insulating layer thereon, e.g.,</pre>
hic technique (EPO)		
		Inorganic layer (EPO)Composed of oxide or glassy oxide or oxide based glass (EPO)
	257/E21.278 .	Deposition from gas or vapor (EPO)Deposition of silicon oxide (EPO)On silicon body (EPO)
2 313	313/567 W	, 2 XR) ELECTRIC LAMP AND DISCHARGE DEVICES WITH GAS OR VAPOR .Having hollow cathode
2 355		
2 356	Class 356: 356/337 E	, 1 XR) OPTICS: MEASURING AND TESTING BY PARTICLE LIGHT SCATTERING With photocell detection